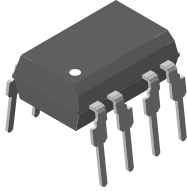
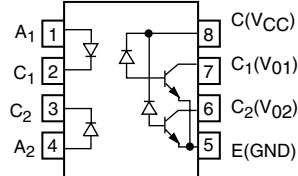


High Speed Optocoupler, Dual Channel, 1 MBd, Transistor Output



1179071



FEATURES

- Isolation test voltage, 5300 V_{RMS}
- TTL compatible
- Bit rates: 1.0 MBit/s
- High common mode transient immunity
- Bandwidth 2.0 MHz
- Open collector output
- Lead (Pb)-free component
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC


RoHS
COMPLIANT

DESCRIPTION

The SFH6325/SFH6326 are dual channel optocouplers with a GaAlAs infrared emitting diode, optically coupled with an integrated photo detector which consists of a photo diode and a high-speed transistor in a DIP-8 plastic package. Signals can be transmitted between two electrically separated circuits up to frequencies of 2.0 MHz. The potential difference between the circuits to be coupled should not exceed the maximum permissible reference voltages.

AGENCY APPROVALS

- UL1577, file no. E52744 system code H or J, double protection

ORDER INFORMATION

PART	REMARKS
SFH6325	CTR > 7.0 %, DIP-8
SFH6326	CTR > 19 %, DIP-8
SFH6325-X009	CTR > 7.0 %, SMD-8 (option 9)
SFH6326-X006	CTR > 19 %, DIP-8 400 mil (option 6)
SFH6326-X007	CTR > 19 %, SMD-8 (option 7)
SFH6326-X009	CTR > 19 %, SMD-8 (option 9)

Note

For additional information on the available options refer to option information.

ABSOLUTE MAXIMUM RATINGS ⁽¹⁾

PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
INPUT				
Reverse voltage		V _R	4.5	V
Forward continuous current		I _F	25	mA
Peak forward current	t = 1.0 ms, duty cycle 50 %	I _{FM}	50	mA
Maximum surge forward current	t ≤ 1.0 μs, 300 pulses/s	I _{FSM}	1.0	A
Derate linearly from 25 °C			0.6	mW/°C
Power dissipation	T _{amb} ≤ 70 °C	P _{diss}	50	mW
OUTPUT				
Supply voltage		V _S	- 0.5 to 30	V
Output voltage		V _O	- 0.5 to 25	V
Collector output current		I _{CO}	8.0	mA
Derate linearly from 25 °C			1.33	mW/°C
Power dissipation	T _{amb} ≤ 70 °C	P _{diss}	50	mW

ABSOLUTE MAXIMUM RATINGS ⁽¹⁾				
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
COUPLER				
Isolation test voltage	$t = 1.0 \text{ s}$	V_{ISO}	5300	V_{RMS}
Pollution degree (DIN VDE 0109)			2	
Creepage distance			≥ 7	mm
Clearance distance			≥ 7	mm
Derate linearly from 25 °C			1.93	mW/°C
Total package dissipation		P_{tot}	145	mW
Comparative tracking index per DIN IEC112/VDE 0303 part 1, group IIIa per DIN VDE 6110			175	
Isolation resistance	$V_{\text{IO}} = 500 \text{ V}, T_{\text{amb}} = 25 \text{ °C}$	R_{IO}	$\geq 10^{12}$	Ω
	$V_{\text{IO}} = 500 \text{ V}, T_{\text{amb}} = 100 \text{ °C}$	R_{IO}	$\geq 10^{11}$	Ω
Storage temperature range		T_{stg}	- 55 to + 125	°C
Ambient temperature range		T_{amb}	- 55 to +100	°C
Soldering temperature ⁽²⁾	max. 10 s, dip soldering distance to seating plane $\geq 1.5 \text{ mm}$	T_{sld}	260	°C

Notes

⁽¹⁾ $T_{\text{amb}} = 25 \text{ °C}$, unless otherwise specified.

Stresses in excess of the absolute maximum ratings can cause permanent damage to the device. Functional operation of the device is not implied at these or any other conditions in excess of those given in the operational sections of this document. Exposure to absolute maximum ratings for extended periods of the time can adversely affect reliability.

⁽²⁾ Refer to reflow profile for soldering conditions for surface mounted devices (SMD). Refer to wave profile for soldering conditions for through hole devices (DIP).

ELECTRICAL CHARACTERISTICS ⁽¹⁾							
PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT
INPUT ⁽²⁾							
Forward voltage	$I_{\text{F}} = 16 \text{ mA}$		V_{F}		1.6	1.9	V
Breakdown voltage	$I_{\text{R}} = 10 \text{ }\mu\text{s}$		V_{BR}	4.5			V
Reverse current	$V_{\text{R}} = 4.5 \text{ V}$		I_{R}		0.5	10	μA
Capacitance	$V_{\text{R}} = 0 \text{ V}, f = 1.0 \text{ MHz}$		C_{O}		125		pF
Temperature coefficient of forward voltage	$I_{\text{F}} = 16 \text{ mA}$		$\Delta V_{\text{F}}/\Delta T_{\text{amb}}$		- 1.7		mV/°C
OUTPUT							
Logic low supply current	$I_{\text{F}} = 16 \text{ mA}, V_{\text{O}} = \text{open}, V_{\text{CC}} = 4.5 \text{ V}$		I_{CCL}		100	200	μA
Supply current, logic high	$I_{\text{F}} = 0 \text{ mA}, V_{\text{O}} = \text{open}, V_{\text{CC}} = 15 \text{ V}$		I_{CCH}		0.01	4.0	μA
Logic low output voltage	$I_{\text{F}} = 16 \text{ mA}, V_{\text{CC}} = 4.5 \text{ V}, I_{\text{O}} = 1.1 \text{ mA}$	SFH6325	V_{OL}		0.1	0.5	V
	$I_{\text{F}} = 16 \text{ mA}, V_{\text{CC}} = 4.5 \text{ V}, I_{\text{O}} = 3.0 \text{ mA}$	SFH6326	V_{OL}		0.1	0.5	V
Logic high output current	$I_{\text{F}} = 0 \text{ mA}, V_{\text{O}} = V_{\text{CC}} = 5.5 \text{ V}$		I_{OH}		3.0	500	nA
	$I_{\text{F}} = 0 \text{ mA}, V_{\text{O}} = V_{\text{CC}} = 15 \text{ V}$		I_{OH}			50	μA
Channel to channel ⁽³⁾ crosstalk	$I_{\text{F}} = 16 \text{ mA}, V_{\text{O}} = V_{\text{CC}} = 5.5 \text{ V}$		$I_{\text{OH-XT}}$			500	nA
COUPLER							
Capacitance (input to output)	$f = 1.0 \text{ MHz}$		C_{IO}		0.6		pF

Notes

⁽¹⁾ $T_{\text{amb}} = 25 \text{ °C}$, unless otherwise specified.

Minimum and maximum values are testing requirements. Typical values are characteristics of the device and are the result of engineering evaluation. Typical values are for information only and are not part of the testing requirements.

⁽²⁾ $T_{\text{amb}} = 0 \text{ °C}$ to 70 °C, unless otherwise specified.

⁽³⁾ To measure crosstalk, turn on the LED for channel 1 and the output current for channel 2 in logic high. Repeat for channel 2.

**CURRENT TRANSFER RATIO**

PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT
Current transfer ratio	$I_F = 16 \text{ mA}$, $V_{CC} = 4.5 \text{ V}$, $V_O = 0.4 \text{ V}$	SFH6325	CTR	5	16		%
		SFH6326	CTR	19	35		%
	$I_F = 16 \text{ mA}$, $V_{CC} = 4.5 \text{ V}$, $V_O = 0.5 \text{ V}$	SFH6325	CTR	5			%
		SFH6326	CTR	15			%

SWITCHING CHARACTERISTICS

PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT
High to low	$I_F = 16 \text{ mA}$, $V_{CC} = 5.0 \text{ V}$, $R_L = 4.1 \text{ k}\Omega$	SFH6325	t_{PHL}		0.3	1.5	μs
	$I_F = 16 \text{ mA}$, $V_{CC} = 5.0 \text{ V}$, $R_L = 1.9 \text{ k}\Omega$	SFH6326	t_{PHL}		0.2	0.8	μs
Low to high	$I_F = 16 \text{ mA}$, $V_{CC} = 5.0 \text{ V}$, $R_L = 4.1 \text{ k}\Omega$	SFH6325	t_{PLH}		0.6	1.5	μs
	$I_F = 16 \text{ mA}$, $V_{CC} = 5.0 \text{ V}$, $R_L = 1.9 \text{ k}\Omega$	SFH6326	t_{PLH}		0.5	0.8	μs

COMMON MODE TRANSIENT IMMUNITY

PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT
CMTI at logic high level output	$I_F = 0 \text{ mA}$, $C_{CM} = 10 \text{ V}_{P-P}$, $V_{CC} = 5.0 \text{ V}$, $R_L = 4.1 \text{ k}\Omega$	SFH6325	CM_H		1000		$\text{V}/\mu\text{s}$
	$I_F = 0 \text{ mA}$, $C_{CM} = 10 \text{ V}_{P-P}$, $V_{CC} = 5.0 \text{ V}$, $R_L = 1.9 \text{ k}\Omega$	SFH6326	CM_H		1000		$\text{V}/\mu\text{s}$
CMTI at logic low level output	$I_F = 16 \text{ mA}$, $C_{CM} = 10 \text{ V}_{P-P}$, $V_{CC} = 5.0 \text{ V}$, $R_L = 4.1 \text{ k}\Omega$	SFH6325	CM_L		1000		$\text{V}/\mu\text{s}$
	$I_F = 16 \text{ mA}$, $C_{CM} = 10 \text{ V}_{P-P}$, $V_{CC} = 5.0 \text{ V}$, $R_L = 1.9 \text{ k}\Omega$	SFH6326	CM_L		1000		$\text{V}/\mu\text{s}$

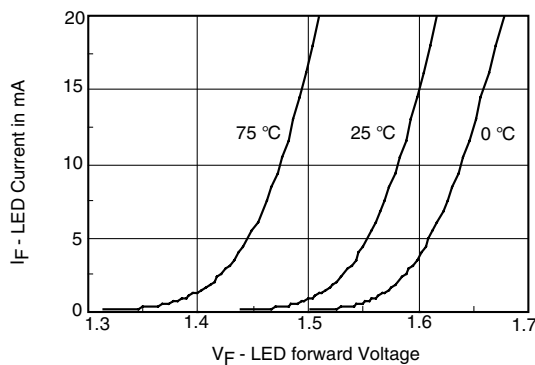
TYPICAL CHARACTERISTICS $T_{amb} = 25^\circ\text{C}$, unless otherwise specified

Fig. 1 - LED Forward Current vs. Forward Voltage

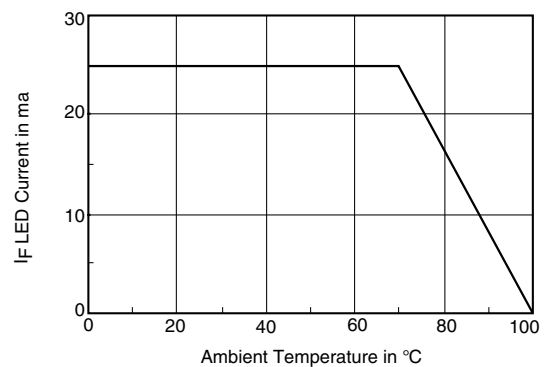
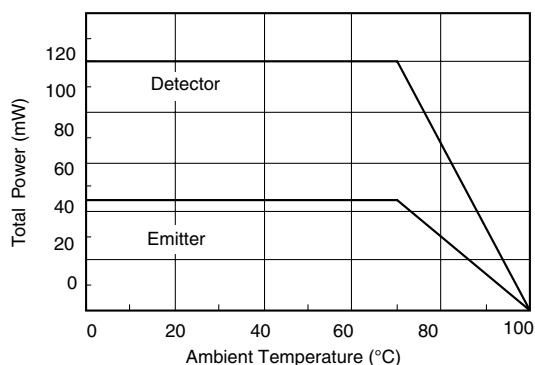
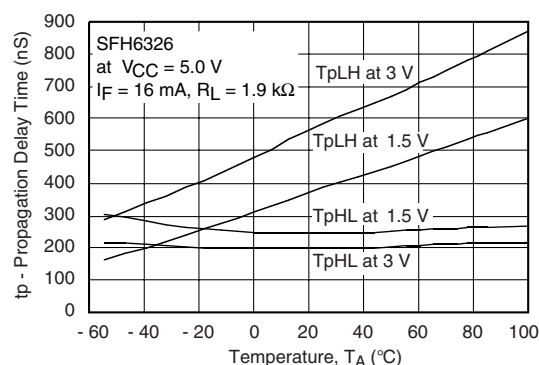


Fig. 2 - Permissible Forward LED Current vs. Temperature



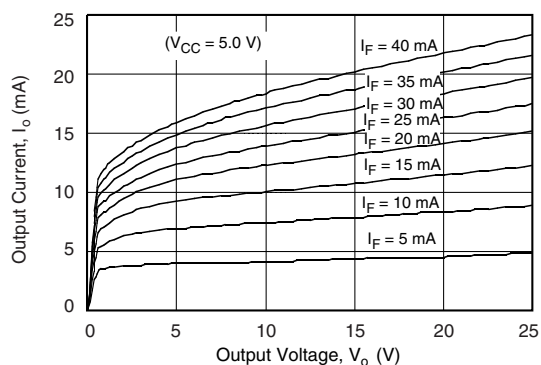
isfh6325_05

Fig. 3 - Permissible Power Dissipation vs. Temperature



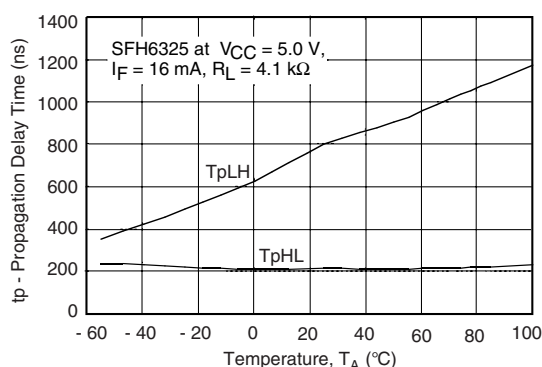
isfh6325_08

Fig. 6 - Propagation Delay vs. Ambient Temperature



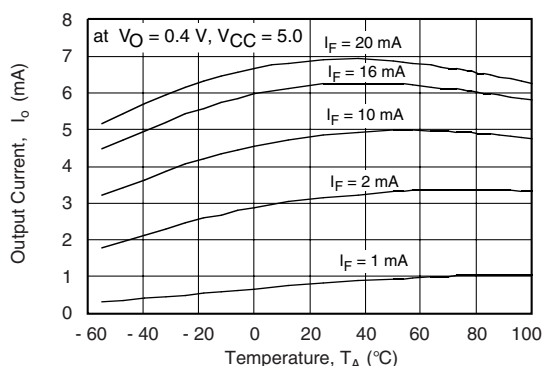
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Fig. 4 - Output Current vs. Output Voltage



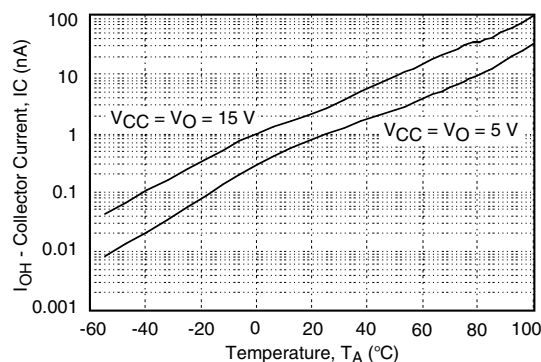
isfh6325_09

Fig. 7 - Propagation Delay vs. Ambient Temperature



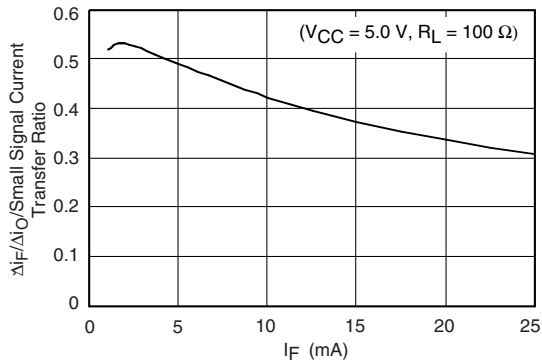
isfh6325_07

Fig. 5 - Output Current vs. Temperature



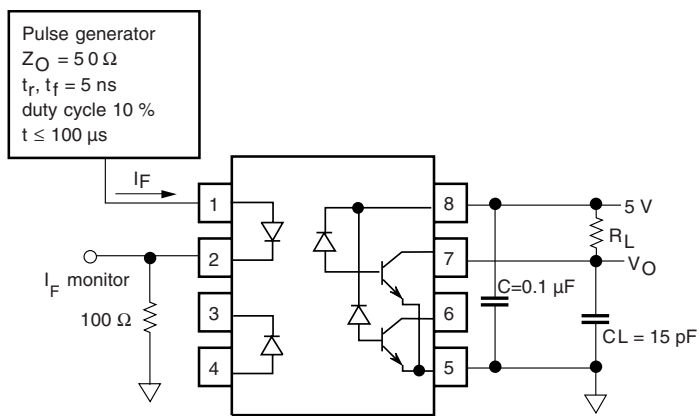
isfh6325_10

Fig. 8 - Logic High Output Current vs. Temperature



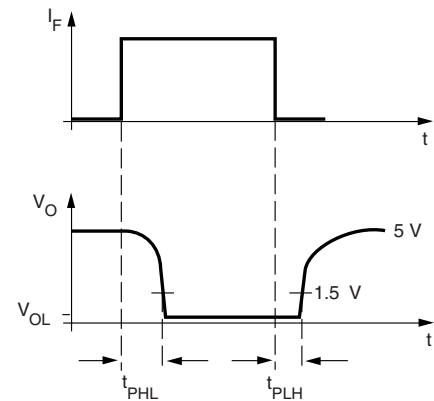
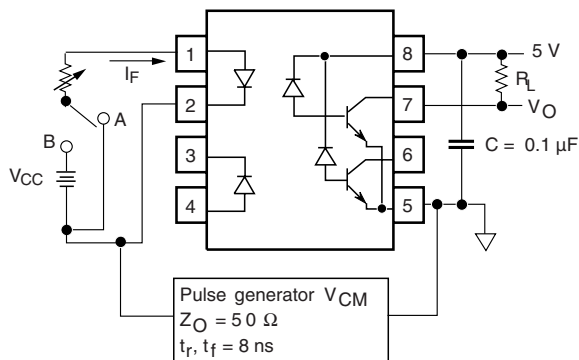
isfh6325_11

Fig. 9 - Small Signal Current Transfer Ratio vs. Input Current



isfh6325_01

Fig. 10 - Switching Time and Test Circuit



isfh6325_02

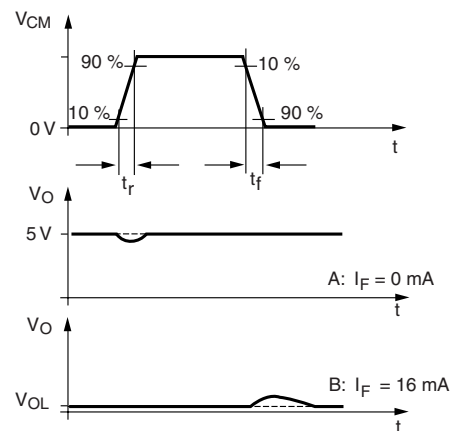
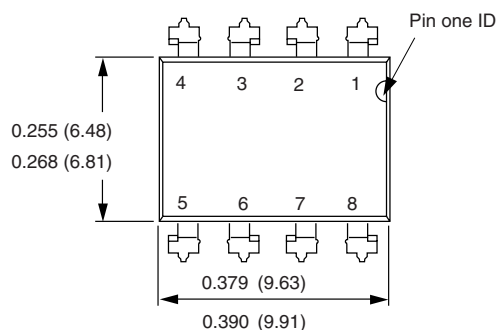
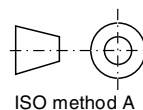
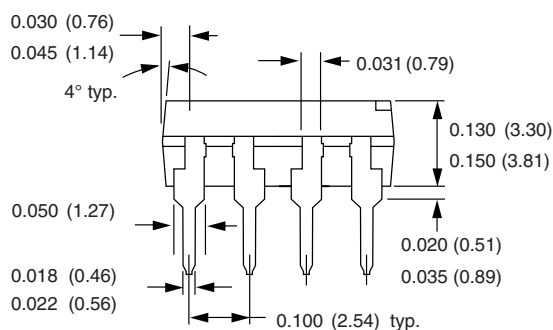
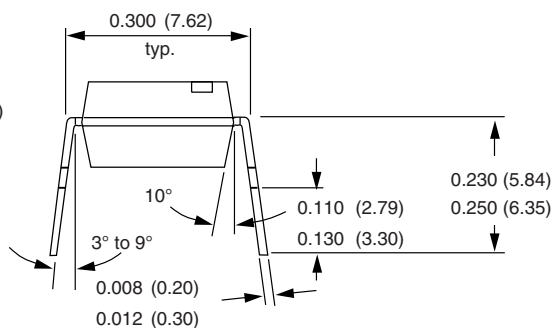


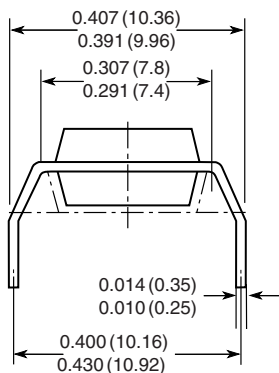
Fig. 11 - Waveform and Test Circuit for Common Mode Transient Immunity

PACKAGE DIMENSIONS in inches (millimeters)

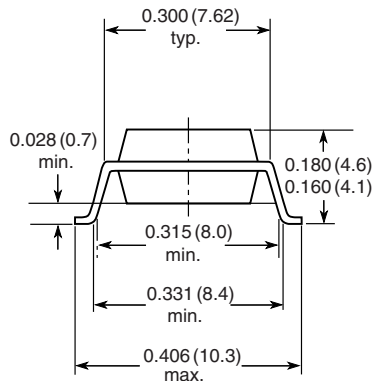


i178006

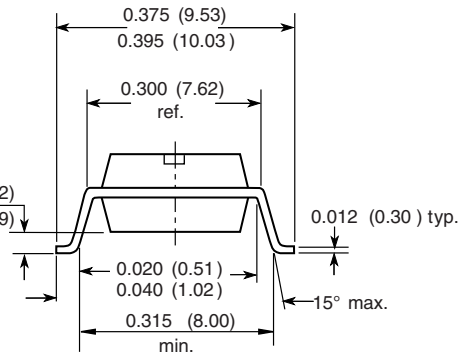
Option 6



Option 7



Option 9



18450

**OZONE DEPLETING SUBSTANCES POLICY STATEMENT**

It is the policy of Vishay Semiconductor GmbH to

1. Meet all present and future national and international statutory requirements.
2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively.
2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA.
3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

We reserve the right to make changes to improve technical design
and may do so without further notice.

Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use Vishay Semiconductors products for any unintended or unauthorized application, the buyer shall indemnify Vishay Semiconductors against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

Vishay Semiconductor GmbH, P.O.B. 3535, D-74025 Heilbronn, Germany



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